

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning on page 12, line 16 as follows:

Devices 111 comprise two devices such as device 109, which may have been formed by use of one or more similar or differing methods, such as those described herein. As shown in devices 111, a portion of the material layers 118 have been selectively removed, in order to expose at least a portion of the interconnect structures 104. Depending at least in part on the material(s) used as a material layer 118, removal may be a selective removal, and may be accomplished by use of a variety of methods, and may depend at least in part on the type of material or combination of materials used to form the material layer 118. Examples of such methods of removal may comprise a chemical mechanical polishing process (CMP), which comprises the use of one or more chemicals and one or more mechanical processes in order to remove particular portions of a layer of material, for example, or a dry etching process, such as reactive ion etching (RIE), although numerous other methods of removal exist, including grinding or spin etching. The material layer 118 may be selectively removed, or polished back, such that at a substantial portion one or more of the interconnect structures 104 are exposed, and in one particular embodiment, the material layer may be polished back such that the top surface of the material layer is slightly lower than the top surface of one or more interconnect structures 104, for example.